

Abstract of the Disclosure

An image sensor having a photo diode with improved sensitivity, junction leakage and electron capacity, and a method for manufacturing the image sensor, are provided. The provided image sensor includes a semiconductor substrate and a p-type photo diode region formed on a selected region of the semiconductor substrate. A first n-type photo diode region is formed underneath the p-type photo diode region, contacting an interface of the p-type photo diode region, and a second n-type photo diode region is formed to surround the first n-type photo diode region. Here, impurities composing the first n-type photo diode region have smaller projection distance and diffusivity than impurities composing the second n-type photo diode region.

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